AG 6A ... AG 6M

Silicon Rectifier Cells

with polysiloxan passivation

AG 6A ... AG 6M

Forward Current: 6 A

Reverse Voltage: 50 to 1000 V

Publish Data

Features

Mechanical Data

- Weight approx. 0.3g
- 2) I_F = 6A, Tj = 25ºC

Type	Repetitive peak reverse voltage V_{RRM} V	Surge peak reverse voltage V_{RSM} V	Max. reverse recovery time I_F = A, I_R = A, I_{RR} = A, t_{rr} ns	Max. forward voltage V_F 2)
AG 6A	50	80		0,9
AG 6B	100	130		0,9
AG 6D	200	250		0,9
AG 6G	400	450		0,9
AG 6J	600	700		0,9
AG 6K	800	1000		0,9
AG 6M	1000	1300		0,9

Absolute Maximum Ratings	T_c = 25ºC unless otherwise specified		
Symbol	**Conditions**	**Values**	**Units**
I_{FAV}	Max. averaged fwd. current, R-load, T_A = 100 °C 1)	6	A
I_{FRM}	Repetitive peak forward current f > 15 Hz 1)	40	A
I_{FSM}	Peak forward surge current 50 Hz half sinus-wave 3)	400	A
i²t	Rating for fusing, t < 10 ms 3)	800	A²s
R_{thA}	Max. thermal resistance junction to ambient 1)		K/W
R_{thT}	Max. thermal resistance junction to terminals 1)		K/W
T_j	Operating junction temperature	-50 ... +150ºC	°C
T_s	Storage temperature	-50 ... +150ºC	°C

Characteristics	T_c = 25ºC unless otherwise specified		
Symbol	**Conditions**	**Values**	**Units**
I_R	Maximum leakage current, T_j = 25 °C; $V_R = V_{RRM}$	10	µA
	T_j = 100 °C; $V_R = V_{RRM}$	5	mA
C_J	Typical junction capacitance (at MHz and applied reverse voltage of V)		pF
Q_{rr}	Reverse recovery charge (U_R = V; I_F = A; dI_F/dt = A/ms)		µC
E_{RSM}	Non repetitive peak reverse avalanche energy (I_R = mA; T_j = °C; inductive load switched off)		mJ

Dimensions in mm